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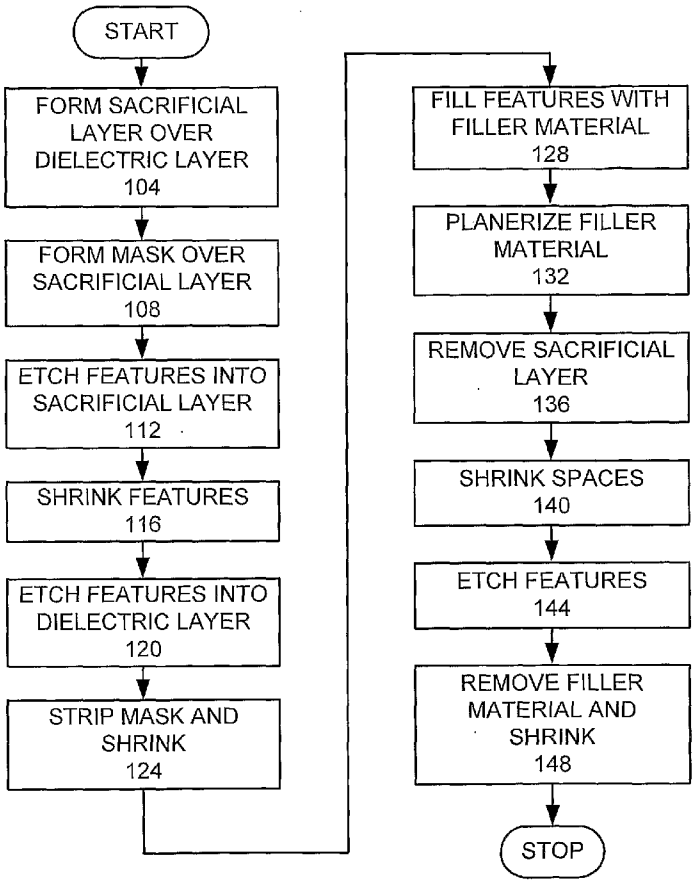
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(54) Title: SELF-ALIGNED PITCH REDUCTION



(57) Abstract: A method providing features in a etch layer is provided. A sacrificial layer is formed over the etch layer. A set of sacrificial layer features is etched into the sacrificial layer. A first set of etch layer features is etched into the etch layer through the sacrificial layer. The first set of etch layer features and the set of sacrificial layer features are filled with a filler material. The sacrificial layer is removed. The widths of the spaces between the parts of the filler material are shrunk with a shrink sidewall deposition. A second set of etch layer features is etched into the etch layer through the shrink sidewall deposition. The filler material and shrink sidewall deposition are removed.

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